



**Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	$R_{thJC}$	-	-	2.1	° C/W
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	62.5	° C/W
Soldering temperature, wavesoldering for 10s	$T_{sold}$	-	-	265	° C

**Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	65			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1.2		2.5	V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS} = 60V, V_{GS} = 0V$			1.0	$\mu A$
Gate- Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$	nA
Static Drain-source On Resistance		$V_{GS} = 10V, I_D = 10A$		8	10	m
		$V_{GS} = 4.5V, I_D = 5A$		11	13	m
Forward Transconductance	$g_{FS}$	$V_{DS} = 25V, I_D = 10A$		14		S
Source-drain voltage	$V_{SD}$	$I_S = 10A$			1.28	V

**Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	$C_{iss}$	$f = 1MHz$	-	960	-	pF
Output capacitance	$C_{oss}$		-	460	-	

Reverse transfer capacitance





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